

**In The Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Original) A porous substrate, comprising a plurality of porous layers thereon, wherein the average opening diameter of pores in a porous layer of said plurality of porous layers positioned in an outermost surface is smaller than the average diameter of pores in a porous layer of said plurality of porous layers positioned on a substrate side relative to said porous layer positioned in said outermost surface.
2. (Original) A porous substrate, comprising a plurality of porous layers thereon, wherein the average opening diameter of pores in a porous layer of said plurality of porous layers positioned in an outermost surface is smaller than the average diameter of pores in a porous layer of said plurality of porous layers positioned on a substrate side relative to said porous layer positioned in said outermost surface; and the volume porosity of said plurality of porous layers is 10%-90%.
3. (Original) A porous substrate, comprising two porous layers thereon, wherein the average opening diameter of pores in a first porous layer of said two porous layers positioned in an outermost surface is smaller than the average diameter of pores in a second porous layer positioned on a substrate side relative to said first porous layer; and more than 50% of said pores in said first porous layer penetrate from the surface of said first porous layer to the interface between said first and second porous layer.
4. (Original) A porous substrate, comprising two porous layers thereon, wherein the average opening diameter of pores in a first porous layer of said two porous layers positioned in an outermost surface is smaller than the average diameter of pores in a

second porous layer positioned on a substrate side relative to said first porous layer; more than 50% of said pores in said first porous layer penetrate from the surface of said first porous layer to the interface between said first and second porous layer; and the volume porosity of said first and second porous layer is 10%-90%.

5. (Original) The porous substrate according to claim 3, wherein said first porous layer comprises a metal material.

6. (Original) The porous substrate according to claim 3, wherein said first porous layer comprises a metal oxide, a metal nitride, or a metal carbide.

7. (Original) The porous substrate according to claim 3, wherein said second porous layer comprises a semiconductor material.

8. (Original) The porous substrate according to claim 3, wherein said second porous layer comprises a group III nitride series compound semiconductor material.

9. (Original) The porous substrate according to claim 3, wherein said first porous layer comprises TiN or Pt, and said second porous layer comprises GaN.

10. (Original) The porous substrate according to claim 3, wherein said average opening diameter of said porosity in said first porous layer is not more than 1  $\mu\text{m}$ .

11. (Original) The porous substrate according to claim 3, wherein the film thickness of said first porous layer is not more than 1  $\mu\text{m}$ .

12. (Withdrawn) A fabrication method for a porous substrate, comprising growing two or more different material layers on a substrate, heating said each layer, and thereby forming two or more porous layers with pores therein.

13. (Original) A GaN series semiconductor layered substrate, comprising a GaN series semiconductor layer grown on a porous substrate defined claim 1.

14. (Withdrawn) A fabrication method for a GaN series semiconductor layered substrate, comprising growing two or more different material layers on a substrate, heating said each layer, thereby forming a porous substrate with two or more porous layers having pores therein, and growing a GaN semiconductor layer on that porous substrate.
15. (Original) A GaN series semiconductor layered substrate, comprising a GaN series semiconductor layer grown on a porous substrate defined in claim 2.
16. (Withdrawn) A GaN series semiconductor layered substrate, comprising a GaN series semiconductor layer grown on a porous substrate defined in claim 3.
17. (Original) A GaN series semiconductor layered substrate, comprising a GaN series semiconductor layer grown on a porous substrate defined in claim 4.